

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

EMH2411R — General-Purpose Switching Device **Applications**

Features

- · Low ON-resistance
- · Best suited for LiB charging and discharging switch
- · Common-drain type
- · 2.5V drive
- · Halogen free compliance
- · Protection diode in

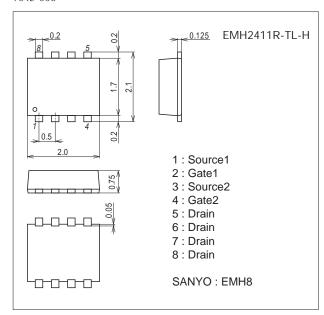
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		30	V
Gate-to-Source Voltage	V _{GSS}		±12	V
Drain Current (DC)	ID		5	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	60	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² x0.8mm) 1unit	1.3	W
Total Dissipation	PT	When mounted on ceramic substrate (900mm ² ×0.8mm)	1.4	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

unit: mm (typ) 7045-006



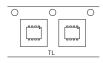
Product & Package Information

• Package : EMH8

• JEITA, JEDEC

• Minimum Packing Quantity : 3,000 pcs./reel

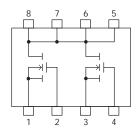
Packing Type: TL



Marking



Electrical Connection



SANYO Semiconductor Co., Ltd.

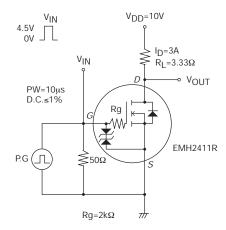
http://semicon.sanyo.com/en/network

EMH2411R

Electrical Characteristics at Ta=25°C

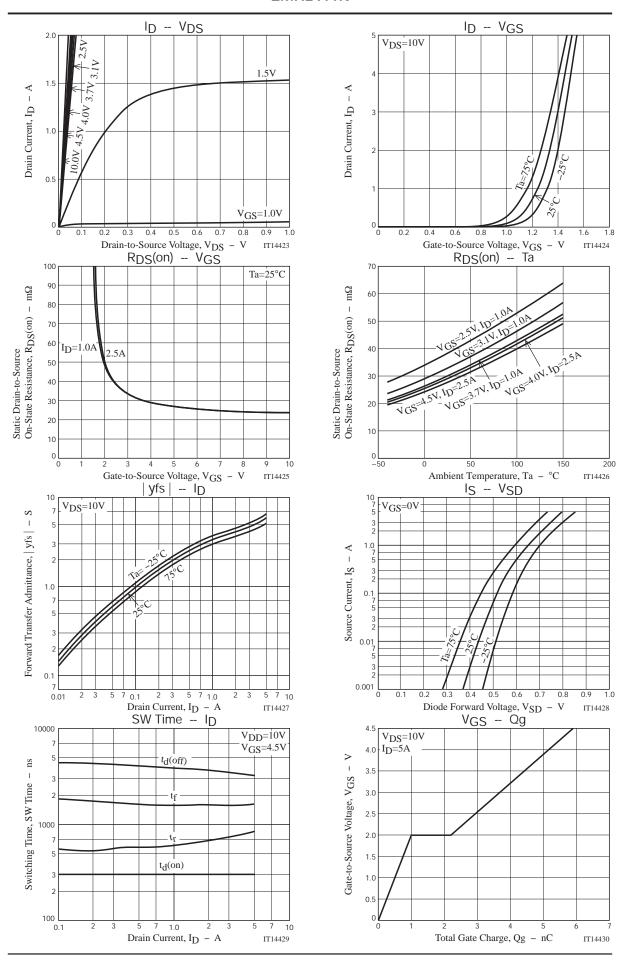
Parameter	Cumbol	Conditions	Ratings			Unit
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	30			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =30V, V _{GS} =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	0.5		1.3	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =3A	3	5		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=2.5A, VGS=4.5V	19.5	28	36.5	mΩ
	R _{DS} (on)2	I _D =2.5A, V _{GS} =4V	20	29	38	mΩ
	RDS(on)3	ID=1A, VGS=3.7V	21	30	39	mΩ
	R _{DS} (on)4	I _D =1A, V _{GS} =3.1V	21	33	46.5	mΩ
	R _{DS} (on)5	I _D =1A, V _{GS} =2.5V	22.5	38	54	mΩ
Turn-ON Delay Time	t _d (on)			300		ns
Rise Time	t _r	See specified Test Circuit		840		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		3200		ns
Fall Time	tf			1650		ns
Total Gate Charge	Qg			5.9		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =4.5V, I _D =5A		1		nC
Gate-to-Drain "Miller" Charge	Qgd			1.2		nC
Diode Forward Voltage	V _{SD}	I _S =5A, V _{GS} =0V		0.8	1.2	V

Switching Time Test Circuit

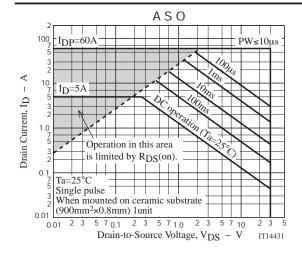


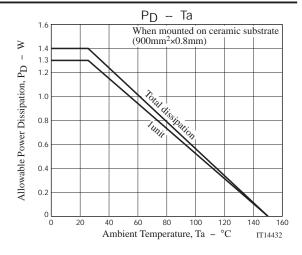
Ordering Information

Device Package		Shipping	memo	
EMH2411R-TL-H	EMH8	3,000pcs./reel	Pb Free and Halogen Free	



EMH2411R



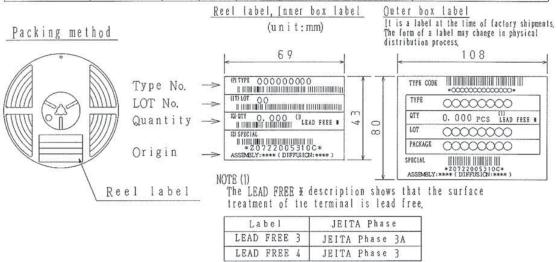


Embossed Taping Specification

EMH2411R-TL-H

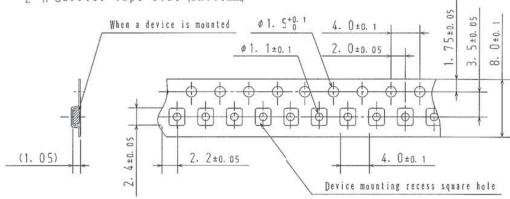
1. Packing Format

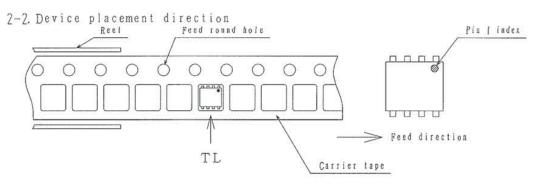
Package Name Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format		
	Type	Reel		Outer box	Inner BOX (C-1)	Outer BOX (A-7)
ЕМН8	MCP4	3, 000	15, 000	90, 000	5 reels contained Dinensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) $440 \times 195 \times 210$



7. Taping configuration

2-1. Carrier tape size (unit:mm)

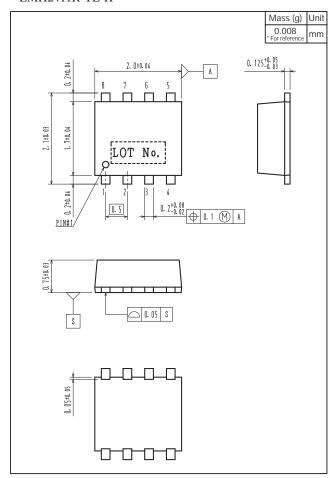




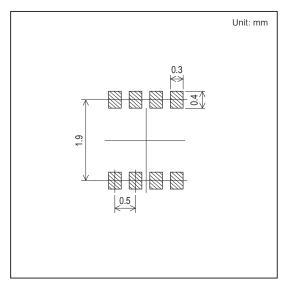
Those with pin 1 index on the feed hole side ·····TL

Outline Drawing

EMH2411R-TL-H



Land Pattern Example



Note on usage: Since the EMH2411R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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